

AMENDMENTS TO THE ABSTRACT

Please cancel the Abstract section of the specification and replace with the following:

A mask vapor deposition system includes an electrostatic chucking mechanism for attracting a subject for deposition using electrostatic attraction, a silicon deposition mask that is brought into close contact with a face of the deposition subject for depositing a deposition material in a predetermined pattern, the face being reverse to that of the deposition subject attracted by the electrostatic chucking mechanism, an evaporation source for evaporating the deposition material, and a vacuum chamber, wherein the mechanism, mask, and source are at least placed in the vacuum chamber.